



# MP2N60ER

## 主要参数MAIN CHARACTERISTICS

|                                      |             |
|--------------------------------------|-------------|
| $I_D$                                | 2A          |
| $V_{DS}$                             | 600V        |
| $R_{DS(on)-max}$<br>( $V_{GS}=10V$ ) | $3.3\Omega$ |
| $Q_g-Typ$                            | 9.8nC       |

### 用途

- 高频开关电源
- 变频家电
- LED 电源

### APPLICATIONS

- High efficiency switch mode power supplies
- Variable frequency household appliance
- LED power supplies

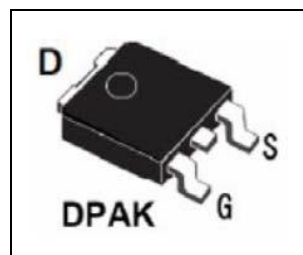
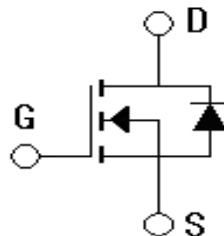
### 产品特性

- 低栅极电荷
- 低  $Cr_{ss}$ (1.4pF typ)
- 开关速度快
- 产品全部经过雪崩测试
- RoHS 产品

### FEATURES

- Low gate charge
- Low  $Cr_{ss}$ (1.4pF typ)
- Fast switching
- 100% avalanche tested
- RoHS product

## 封装 Package



## 订货信息 ORDER MESSAGE

| 订货型号 Order codes      |                            |                       |                            | 印记<br>Marking | 封装<br>Package |
|-----------------------|----------------------------|-----------------------|----------------------------|---------------|---------------|
| 有卤-条管<br>Halogen-Tube | 无卤-条管<br>Halogen-Free-Tube | 有卤-编带<br>Halogen-Reel | 无卤-编带<br>Halogen-Free-Reel |               |               |
| N/A                   | MP2N60ER-R-BR              | N/A                   | MP2N60ER-R-AR              | MP2N60ER      | DPAK          |



绝对最大额定值ABSOLUTE RATINGS( $T_c=25^{\circ}\text{C}$ )

| 项目<br>Parameter                                             | 符号<br>Symbol                                                         | 数值<br>Value          | 单位<br>Unit            |
|-------------------------------------------------------------|----------------------------------------------------------------------|----------------------|-----------------------|
| 最高漏极-源极直流电压<br>Drain-Source Voltage                         | $V_{DSS}$                                                            | 600                  | V                     |
| 连续漏极电流<br>Drain Current-continuous                          | $I_D$ $T=25^{\circ}\text{C}$<br>$T=100^{\circ}\text{C}$              | 2                    | A                     |
|                                                             |                                                                      | 1.2                  | A                     |
| 最大脉冲漏极电流 (注1)<br>Drain Current – pulse (note 1)             | $I_{DM}$                                                             | 8                    | A                     |
| 最高栅源电压<br>Gate-Source Voltage                               | $V_{GSS}$                                                            | $\pm 30$             | V                     |
| 单脉冲雪崩能量 (注2)<br>Single Pulsed Avalanche Energy (note 2)     | $E_{AS}$                                                             | 12                   | mJ                    |
| 二极管反向恢复最大电压变化速率 (注3)<br>Peak Diode Recovery dv/dt (note 3)  | dv/dt                                                                | 1.2                  | V/ns                  |
| 耗散功率<br>Power Dissipation                                   | $P_D$ $T_c=25^{\circ}\text{C}$<br>-Derate above $25^{\circ}\text{C}$ | 88                   | W                     |
|                                                             |                                                                      | 0.7                  | W/ $^{\circ}\text{C}$ |
| 最高结温及存储温度<br>Operating and Storage Temperature Range        | $T_J, T_{STG}$                                                       | 150; $-55 \sim +150$ | $^{\circ}\text{C}$    |
| 引线最高焊接温度<br>Maximum Lead Temperature for Soldering Purposes | $T_L$                                                                | 300                  | $^{\circ}\text{C}$    |

\*漏极电流由最高结温限制

\*Drain current limited by maximum junction temperature





## 电特性 ELECTRICAL CHARACTERISTICS

| 项目<br>Parameter                                       | 符号<br>Symbol                 | 测试条件<br>Tests conditions                    | 最小<br>Min | 典型<br>Typ | 最大<br>Max | 单位<br>Units   |
|-------------------------------------------------------|------------------------------|---------------------------------------------|-----------|-----------|-----------|---------------|
| 关态特性 Off –Characteristics                             |                              |                                             |           |           |           |               |
| 漏-源击穿电压<br>Drain-Source Voltage                       | $BV_{DSS}$                   | $I_D=250\mu A, V_{GS}=0V$                   | 600       | -         | -         | V             |
| 击穿电压温度特性<br>Breakdown Voltage Temperature Coefficient | $\Delta BV_{DSS}/\Delta T_J$ | $I_D=250\mu A$ , referenced to $25^\circ C$ | -         | 0.6       | -         | V/ $^\circ C$ |
| 零栅压下漏极漏电流<br>Zero Gate Voltage Drain Current          | $I_{DSS}$                    | $V_{DS}=600V, V_{GS}=0V, T_C=25^\circ C$    | -         | -         | 1         | $\mu A$       |
|                                                       |                              | $V_{DS}=480V, V_{GS}=0V, T_C=125^\circ C$   | -         | -         | 100       | $\mu A$       |
| 正向栅极体漏电流<br>Gate-body leakage current, forward        | $I_{GSSF}$                   | $V_{DS}=0V, V_{GS}=30V$                     | -         | -         | 100       | nA            |
| 反向栅极体漏电流<br>Gate-body leakage current, reverse        | $I_{GSSR}$                   | $V_{DS}=0V, V_{GS}=-30V$                    | -         | -         | -100      | nA            |
| 通态特性 On-Characteristics                               |                              |                                             |           |           |           |               |
| 阈值电压<br>Gate Threshold Voltage                        | $V_{GS(th)}$                 | $V_{DS} = V_{GS}, I_D=250\mu A$             | 2         | -         | 4         | V             |
| 静态导通电阻<br>Static Drain-Source On-Resistance           | $R_{DS(ON)}$                 | $V_{GS}=10V, I_D=1.0A$<br>$25^\circ C$      | -         | 2.7       | 3.3       | $\Omega$      |
| 正向跨导<br>Forward Transconductance                      | $g_{fs}$                     | $V_{DS}=40V, I_D=1.0A$<br>(note 4)          | -         | 2.8       | -         | S             |
| 动态特性 Dynamic Characteristics                          |                              |                                             |           |           |           |               |
| 栅极电阻<br>Gate resistance                               | $R_g$                        | $F=1.0MHz$ open drain                       | 7.5       | 10        | 12.5      | $\Omega$      |
| 输入电容<br>Input capacitance                             | $C_{iss}$                    | $V_{DS}=25V,$<br>$V_{GS}=0V,$<br>$f=1.0MHz$ | -         | 555       | -         | pF            |
| 输出电容<br>Output capacitance                            | $C_{oss}$                    |                                             | -         | 39        | -         | pF            |
| 反向传输电容<br>Reverse transfer capacitance                | $C_{rss}$                    |                                             | -         | 1.4       | -         | pF            |





## 电特性 ELECTRICAL CHARACTERISTICS

| 开关特性 Switching Characteristics                                        |                     |                                                                             |   |      |      |    |
|-----------------------------------------------------------------------|---------------------|-----------------------------------------------------------------------------|---|------|------|----|
| 延迟时间 Turn-On delay time                                               | t <sub>d(on)</sub>  | V <sub>DD</sub> =300V,I <sub>D</sub> =2A,R <sub>G</sub> =25Ω<br>(note 4, 5) | - | 7.4  | -    | ns |
| 上升时间 Turn-On rise time                                                | t <sub>r</sub>      |                                                                             | - | 21.8 | -    | ns |
| 延迟时间 Turn-Off delay time                                              | t <sub>d(off)</sub> |                                                                             | - | 30.2 | -    | ns |
| 下降时间 Turn-Off Fall time                                               | t <sub>f</sub>      |                                                                             | - | 27   | -    | ns |
| 栅极电荷总量 Total Gate Charge                                              | Q <sub>g</sub>      | V <sub>DS</sub> =480V ,                                                     | - | 9.8  | -    | nC |
| 栅-源电荷 Gate-Source charge                                              | Q <sub>gs</sub>     | I <sub>D</sub> =2A                                                          | - | 3    | -    | nC |
| 栅-漏电荷 Gate-Drain charge                                               | Q <sub>gd</sub>     | V <sub>GS</sub> =10V (note 4, 5)                                            | - | 2.9  | -    | nC |
| 漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings |                     |                                                                             |   |      |      |    |
| 正向最大连续电流<br>Maximum Continuous Drain<br>-Source Diode Forward Current | I <sub>S</sub>      |                                                                             | - | -    | 2    | A  |
| 正向最大脉冲电流<br>Maximum Pulsed Drain-Source<br>Diode Forward Current      | I <sub>SM</sub>     |                                                                             | - | -    | 8    | A  |
| 正向压降<br>Drain-Source Diode Forward<br>Voltage                         | V <sub>SD</sub>     | V <sub>GS</sub> =0V, I <sub>S</sub> =2A                                     | - | -    | 1.40 | V  |
| 反向恢复时间<br>Reverse recovery time                                       | t <sub>rr</sub>     | V <sub>GS</sub> =0V, I <sub>S</sub> =2A                                     | - | 121  | -    | ns |
| 反向恢复电荷<br>Reverse recovery charge                                     | Q <sub>rr</sub>     | dI <sub>F</sub> /dt=100A/μs (note 4)                                        | - | 174  | -    | nC |

## 热特性 THERMAL CHARACTERISTIC

| 项目<br>Parameter                                    | 符号<br>Symbol  | 数值<br>Value | 单位<br>Unit    |
|----------------------------------------------------|---------------|-------------|---------------|
| 结到管壳的热阻<br>Thermal Resistance, Junction to Case    | $R_{th(j-c)}$ | 1.4         | $^{\circ}C/W$ |
| 结到环境的热阻<br>Thermal Resistance, Junction to Ambient | $R_{th(j-A)}$ | 102         | $^{\circ}C/W$ |

注释:

- 1: 脉冲宽度由最高结温限制
- 2:  $L=0.5mH, I_{AS}=7A, V_{DD}=50V, R_G=25\Omega$ , 起始结温  $T_J=25^{\circ}C$
- 3:  $I_{SD} \leq 2A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$ , 起始结温  $T_J=25^{\circ}C$
- 4: 脉冲测试: 脉冲宽度 $\leq 300\mu s$ , 占空比 $\leq 2\%$
- 5: 基本与工作温度无关

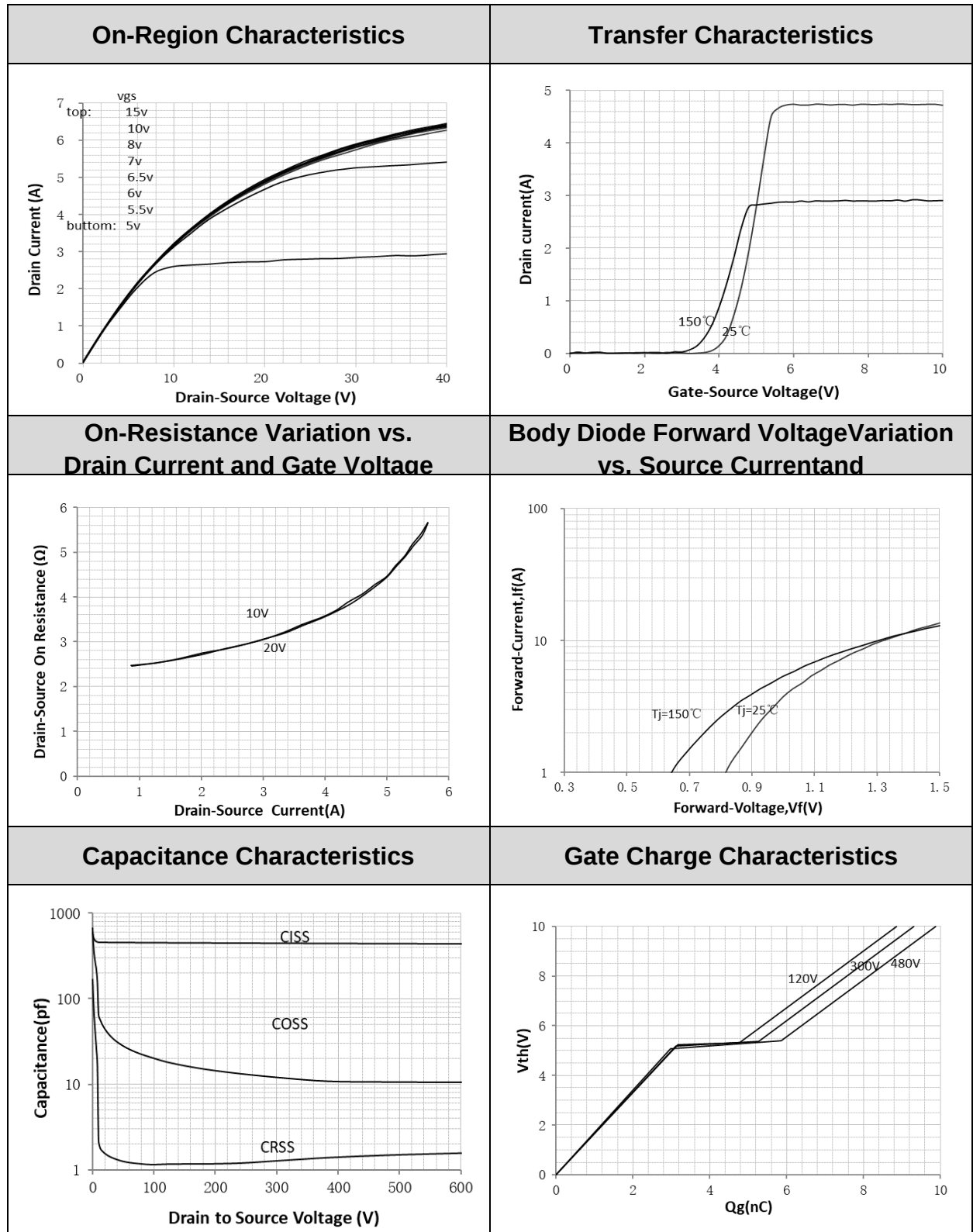
Notes:

- 1: Pulse width limited by maximum junction temperature
- 2:  $L=0.5mH, I_{AS}=7A, V_{DD}=50V, R_G=25\Omega$ , Starting  $T_J=25^{\circ}C$
- 3:  $I_{SD} \leq 2A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J=25^{\circ}C$
- 4: Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycles  $\leq 2\%$
- 5: Essentially independent of operating temperature



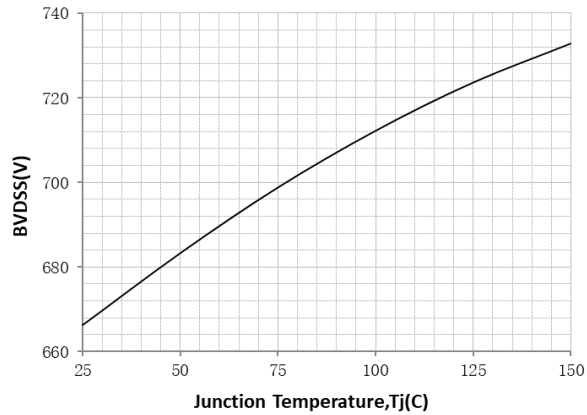
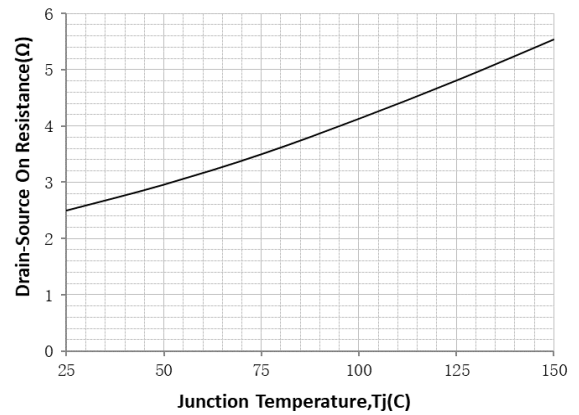
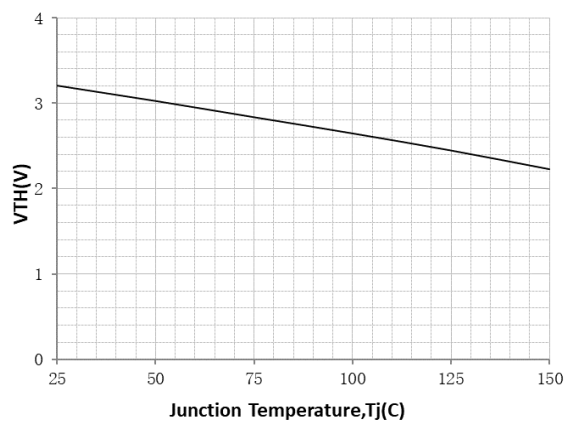
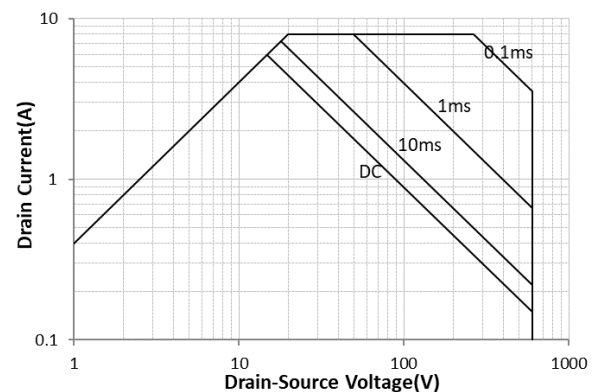
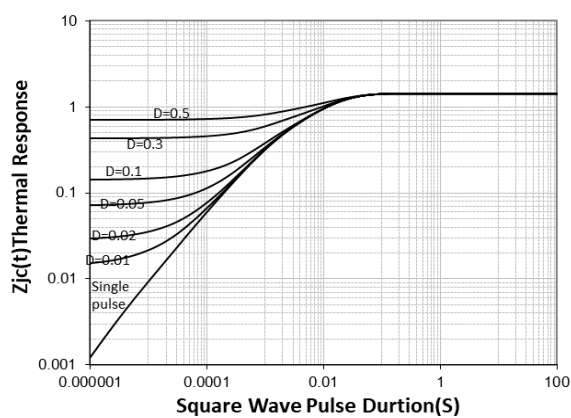


## 特征曲线ELECTRICAL CHARACTERISTICS (curves)





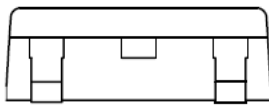
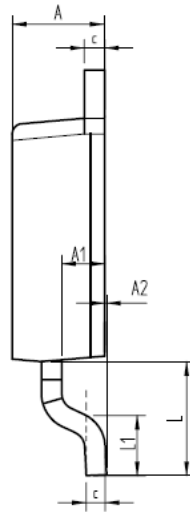
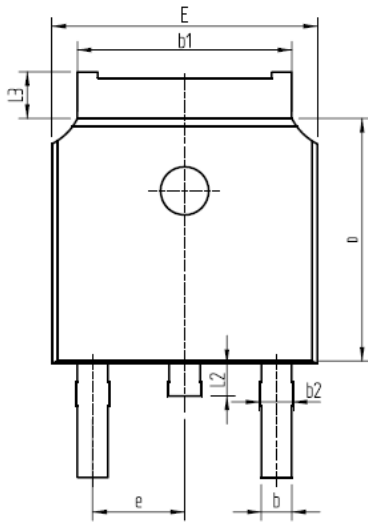
## 特征曲线ELECTRICAL CHARACTERISTICS (curves)

Breakdown Voltage Variation  
vs. TemperatureOn-Resistance Variation  
vs. TemperatureV<sub>TH</sub>  
vs. TemperatureMaximum Safe Operating Area  
For MP2N60ERTransient Thermal Response Curve  
For MP2N60ER



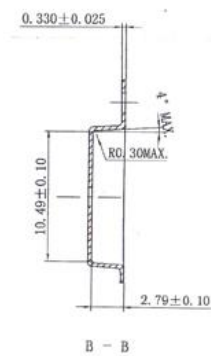
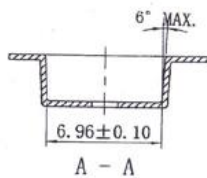
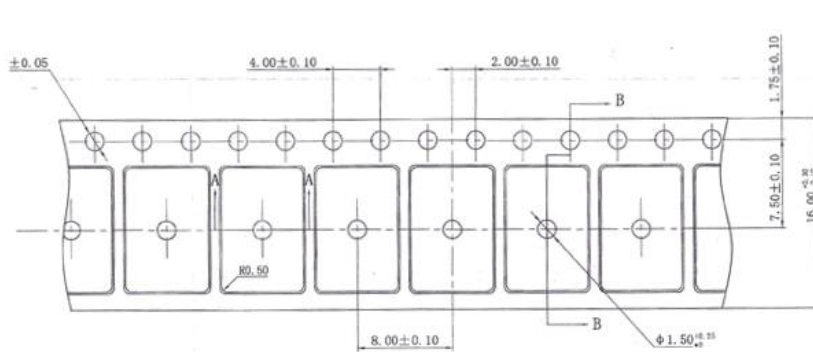
外形尺寸 PACKAGE MECHANICAL DATA  
DPAK

单位 Unit: mm



| SYMBOL | mm       |      |
|--------|----------|------|
|        | MIN      | MAX  |
| A      | 2.16     | 2.41 |
| A1     | 0.97     | 1.17 |
| A2     | 0.00     | 0.15 |
| b      | 0.63     | 0.93 |
| b1     | 5.13     | 5.53 |
| b2     | 0.66     | 0.96 |
| c      | 0.40     | 0.60 |
| D      | 5.80     | 6.40 |
| E      | 6.30     | 6.90 |
| e      | 2.286BSC |      |
| L      | 2.50     | 3.30 |
| L1     | 1.20     | 1.80 |
| L2     | 0.60     | 1.00 |
| L3     | 0.85     | 1.30 |

编带 REEL





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